### TOSHIBA Photocoupler GaAs Ired LED & Photo-Triac

# **TLP363J**

Triac Drivers
Programmable Controllers
AC-Output Modules
Solid State Relays

TOSHIBA TLP363J consists of a zero-voltage-crossing turn-on photo-triac optically coupled to a gallium arsenide infrared-emitting diode in a four-lead plastic DIP package.

This product has a greater capacity to withstand external noise than the TLP361J.

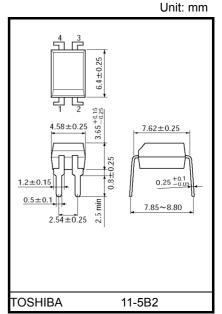
- Peak off-state voltage: 600 V (min)
  Trigger LED current: 10 mA (max)
  On-state current: 100 mA (max)
- On-state current: 100 mA (max)
  Isolation voltage: 5000 Vrms (min)
- Zero crossing function
- UL recognized: UL1577, file No. E67349
- · Option (D4) type

TÜV approved: DIN EN60747-5-2

Certificate No. R50033433

Maximum operating insulation voltage : 890 Vpk Maximum permissible overvoltage : 8000 Vpk

(Note) When an EN60747-5-2 approved type is needed, please designate "Option (D4)."

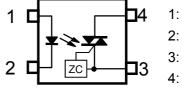


Weight: 0.26 g (typ.)

## •Construction mechanical rating

	7.62 mm pitch TLPXXX type	10.16 mm pitch TLPXXXF type
Creepage distance	7.0 mm (min)	8.0 mm (min)
Clearance	7.0 mm (min)	8.0 mm (min)
Insulation thickness	0.4 mm (min)	0.4 mm (min)

## Pin Configuration (top view)



- 1: Anode
- 2: Cathode
- 3: Triac T1
- 4: Triac T2

## **Absolute Maximum Ratings (Ta = 25°C)**

Characteristic				Rating	Unit	
Forward current			I <sub>F</sub>	50	mA	
	Forward current derating (Ta ≥ 53°C)	ΔI <sub>F</sub> /°C	-0.7	mA /°C		
Ω	Peak forward current (100 µs pulse, 100 pps)		I <sub>FP</sub>	1	Α	
LED	Reverse voltage		V <sub>R</sub>	5	٧	
	Junction temperature		Tj	125	°C	
	Input power dissipation		PD	72	mW	
	Off-state output terminal voltage		$V_{DRM}$	600	V	
	On-state RMS current	Ta = 25°C	I=	100	mA	
		Ta = 70°C	I <sub>T(RMS)</sub>	50		
Detector	On-state current derating (Ta ≥ 25°C)	ΔI <sub>T</sub> /°C	-1.1	mA /°C		
Dete	Peak on-state current (100 µs pulse, 120 pps)	I <sub>TP</sub>	2	Α		
	Peak non-repetitive surge current (Pw =10 ms)	I <sub>TSM</sub>	1.2	Α		
	Junction temperature		Tj	115	°C	
	Output power dissipation	Po	300	mW		
Storage temperature range			T <sub>stg</sub>	-55 to 125	°C	
Ope	Operating temperature range			-40 to 100	°C	
Lea	Lead soldering temperature (10 s)		T <sub>sol</sub>	260	°C	
Isolation voltage (AC,1 minute, R.H. ≤ 60%) (Note 1)		(Note 1)	BVS	5000	Vrms	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

(Note 1): Pins 1 and 2 are shorted together and pins 3 and 4 are shorted together.

**Recommended Operating Conditions** 

Characteristic	Symbol	Min	Тур.	Max	Unit
Supply voltage	V <sub>AC</sub>	_	_	240	$V_{ac}$
Forward current	lF	15	20	25	mA
Peak on-state current	I <sub>TP</sub>	_	_	1	Α
Operating temperature	T <sub>opr</sub>	-25	1	85	°C

Note: Recommended operating conditions are given as a design guideline to obtain expected performance of the device. Additionally, each item is an independent guideline respectively. In developing designs using this product, please confirm specified characteristics shown in this document.

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# **Electrical Characteristics (Ta = 25°C)**

	Characteristic	Symbol	Test Condition	Min	Тур.	Max	Unit
	Forward Voltage	V <sub>F</sub>	I <sub>F</sub> = 10 mA	1.0	1.15	1.3	V
LED	Reverse Current	I <sub>R</sub>	V <sub>R</sub> = 5 V	_	_	10	μA
	Capacitance	C <sub>T</sub>	V = 0 V, f = 1 MHz	_	30	_	pF
	Peak off-state current	I <sub>DRM</sub>	V <sub>DRM</sub> = 600 V	1	10	1000	nA
	Peak on-state voltage	V <sub>TM</sub>	I <sub>TM</sub> = 100 mA	_	1.7	3.0	V
Detector	Holding current	lΗ	_	_	0.6	_	mA
Dete	Critical rate of rise of off-state voltage	dv/dt	Vin = 240 Vrms, Ta = 85°C (Note 2)	200	500	_	V/µs
	Critical rate of rise of commutating voltage	dv/dt(c)	Vin = 60 Vrms, I <sub>T</sub> = 15 mA (Note 2)	_	0.2	_	V/µs

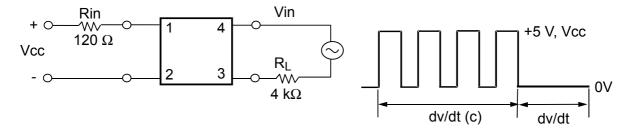
**Coupled Electrical Characteristics (Ta = 25°C)** 

Characteristic	Symbol	Test Condition	Min	Тур.	Max	Unit		
Trigger LED current	I <sub>FT</sub>	V <sub>T</sub> = 3 V	_	_	10	mA		
Inhibit voltage	V <sub>IH</sub>	I <sub>F</sub> = Rated I <sub>F</sub> T	1	_	20	V		
Leakage in inhibited state	Ін	I <sub>F</sub> = Rated I <sub>FT</sub> V <sub>T</sub> = Rated V <sub>DRM</sub>		200	600	μΑ		
Turn-on time	ton	$V_D$ =3 $\rightarrow$ 1.5 V , $R_L$ = 20 $\Omega$ $I_F$ = Rated $I_{FT}$ X1.5	_	30	100	μs		
Impulse noise durability	V <sub>N</sub>	$t_N$ =1μs, Snuber condition 100 $\Omega$ +0.033 $\mu$ F (Note.3)	_	2000	_	٧		

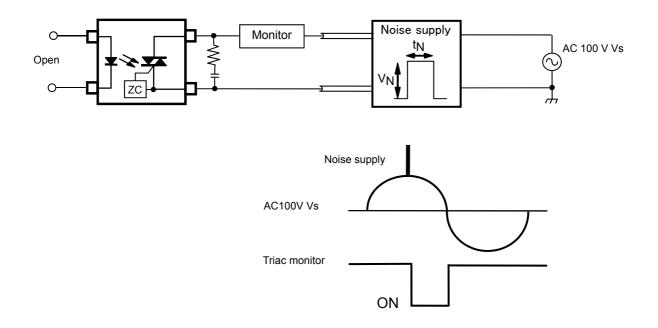
# **Isolation Characteristics (Ta = 25°C)**

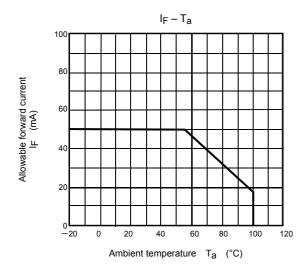
Characteristic	Symbol	Test Condition	Min	Тур.	Max	Unit
Capacitance (input to output)	CS	V <sub>S</sub> = 0 V, f = 1 MHz	_	0.8	_	pF
Isolation resistance	R <sub>S</sub>	V <sub>S</sub> = 500 V, R.H.≤ 60%	1×10 <sup>12</sup>	10 <sup>14</sup>	_	Ω
Isolation voltage	BVS	AC , 1 minute	5000	_	_	\/rma
		AC , 1 second, in oil	_	10000	_	Vrms
		DC , 1 minute, in oil	_	10000	_	Vdc

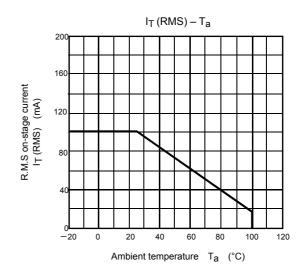
(Note 2): dv/dt test circuit

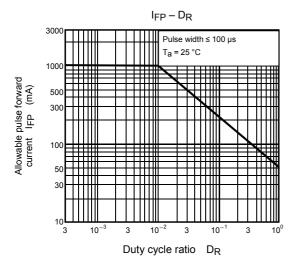


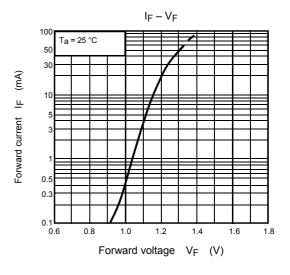
(Note 3): impulse noise durability test circuit

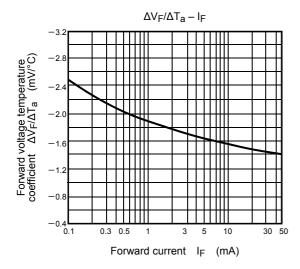


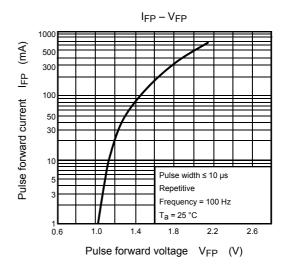




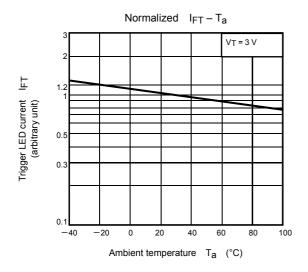


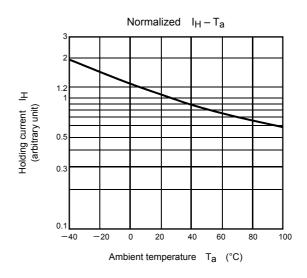


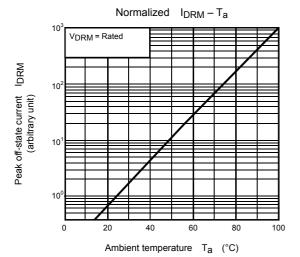


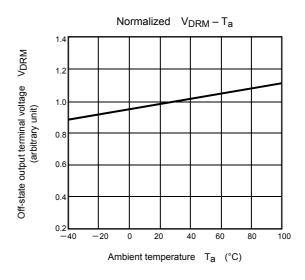


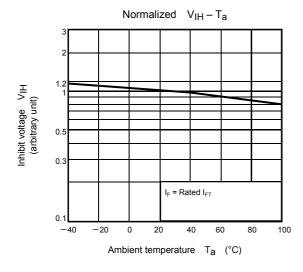
<sup>\*:</sup> The above graphs show typical characteristics.

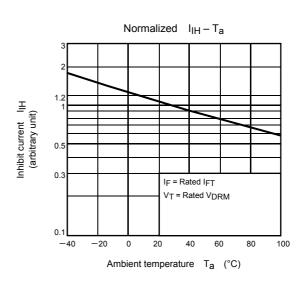












<sup>\*:</sup> The above graphs show typical characteristics.

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